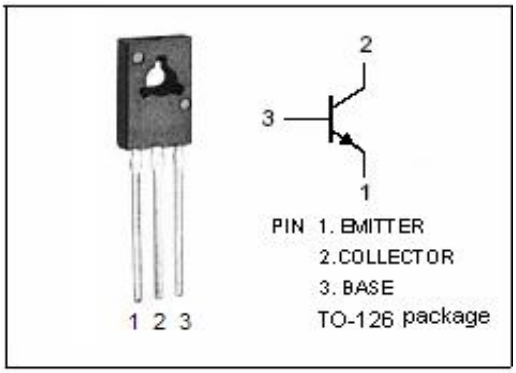
isc Silicon NPN Power Transistor 2SC4001



DESCRIPTION

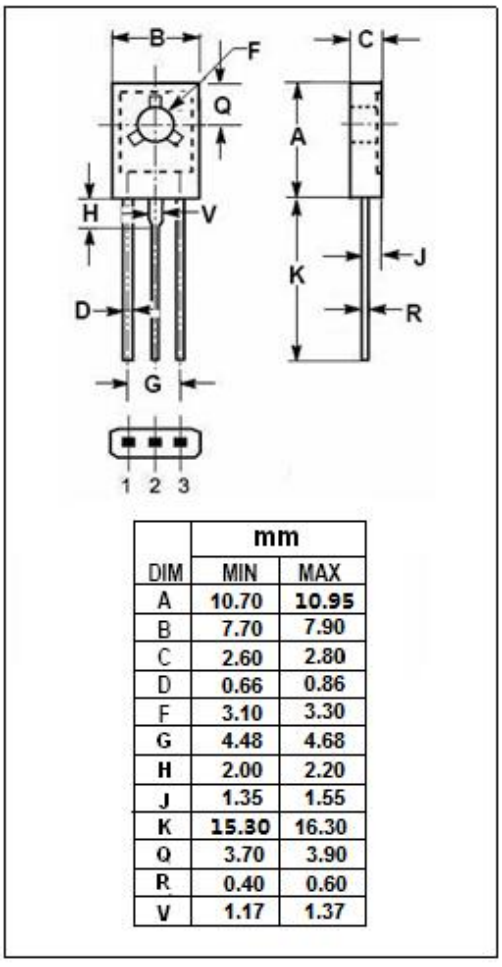
- The 2SC4001is designed for uses of high-resolution monitor TV applications.This makes it possible to raise the video band Of high-resolution monitor TVs to 50MHz.
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

FEATURES

- Collector–Emitter Sustaining Voltage–
  : V_{CBO} = 300 V(Min)
- Complement to Type 2SA1546

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	300	V
V_{CEO}	Collector-Emitter Voltage	250	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	0.1	A
P_C	Collector Power Dissipation T_C=25℃	7	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	mm MAX
A	10.70	10.95
B	7.70	7.90
C	2.60	2.80
D	0.66	0.86
F	3.10	3.30
G	4.48	4.68
H	2.00	2.20
J	1.35	1.55
K	15.30	16.30
Q	3.70	3.90
R	0.40	0.60
V	1.17	1.37

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ELECTRICAL CHARACTERISTICS

T_C =25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
I_{CBO}	Collector Cutoff Current	V_{CB}= 200V; I_E= 0		100	nA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 3V; I_C= 0		100	nA
h_{FE}	DC Current Gain	I_C= 10m A ; V_{CE}=10V	60		300
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 10mA ;I_B=1mA		0.3	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 10mA ;I_B= 1mA		1.2	V
f_T	Current-Gain—Bandwidth Product	I_E= 30mA ; V_{CE}= 30V	200		MHz
C_{OB}	Output Capacitance	I_E= 0 ; V_{CB}= 30V;f_{test}= 1.0MHz		3.5	pF

◆ **h_{FE} Classifications**

M	L	K
60-120	100-200	160-300